

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	935	257/786.ccls. and @ay<1999	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/08/12 06:54
2	BRS	L2	272	loc and memory and array and pad	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/08/12 06:55
3	BRS	L3	0	gan and (ingan gainn) and (algan gaaln) and clad and (quantum adj well) and @ay<1995	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/08/12 07:37
4	BRS	L4	416	gan and ((laser) (light adj emitting adj diode)) and @ay<1995	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/08/12 07:38
5	BRS	L5	40	4 and (quantum adj well)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/08/12 07:39

8/7/02

Search	L No.	Hits	Text Search			Data Bases
BRS	L1	94	(light adj emitting adj (diode device)) and ((ingan gainn) near5 (mqw ((multi multiple) adj quantum adj well)))		8/7/02 15:05	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L2	22	1 and second adj clad\$4		8/7/02 15:06	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L5	141	((ingan gainn) near5 (mqw ((multi multiple) adj quantum adj well)))		8/7/02 15:48	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L6	26	5 and second adj clad\$4		8/7/02 15:06	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L7	129	((gan) near5 (mqw ((multi multiple) adj quantum adj well)))		8/7/02 15:48	USPAT; EPO; JPO; Derwent; IBM TDB

[illegible]

Application No. 09/809038

GaN LED w/ MQW - (InGaN/InGaN)

East Search

2/18/02

Search	L No.	Hits	Text Search		Data Bases
BRS		205	((light adj emitting adj (diode device))) and (quantum adj well) and (gan ingan algan gainn gaaln)) and barrier	2/18/02 11:32	USPAT; EPO; JPO; Derwent; IBM TDB
BRS		11	((light adj emitting adj (diode device))) and (quantum adj well) and (gan ingan algan gainn gaaln)) and @ay<1995) and barrier	2/17/02 21:15	USPAT; EPO; JPO; Derwent; IBM TDB
IS&R	L15	6180	("257/81,84,88,92,93,98,99,100,690,698,700").CCLS.	2/18/02 11:46	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L16	107	15 and (mqw (multi\$4 adj quantum adj well))	2/18/02 11:48	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L17	29	16 and (gan algan ingan gaaln gainn)	2/18/02 11:52	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L18	2	17 and @ay<1995	2/18/02 11:52	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L23	1365	((light adj emitting adj (diode device))) and (gan ingan algan gainn gaaln))	2/18/02 12:21	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L24	236	23 and @ay<1995	2/18/02 12:22	USPAT; EPO; JPO; Derwent; IBM TDB

Search Result

USPAT	Date	Page	Title	CI/Sub	CI/Sub	Inventor
JP 07162038 A	19950623	5	GALLIUM NITRIDE COMPOUND SEMICONDUCTOR LIGHT EMITTING DIODE			NAKAMURA, SHUJI , IWASA, SHIGETO
JP 2000261037 A	20000922	8	SEMICONDUCTOR LIGHT EMITTING DEVICE			KANEIWA, SHINJI
US 4862471 A	19890829	4	Semiconductor light emitting device	372/45	257/191 ; 257/22	Pankove, Jacques I.
US 5237182 A	19930817	13	Electroluminescent device of compound semiconductor with buffer layer	257/15	257/101 ; 257/103 ; 257/94 ; 257/96	Kitagawa, Masahiko , et al.
US 5338944 A	19940816	9	Blue light-emitting diode with degenerate junction structure	257/76	257/101 ; 257/102 ; 257/103 ; 257/77	Edmond, John A. , et al.
US 5432808 A	19950711	16	Compound semiconductor light-emitting device	372/45	257/77 ; 372/44	Hatano, Ako , et al.
US 5537433 A	19960716	21	Semiconductor light emitter	372/45	257/98 ; 372/43	Watanabe, Masanori
US 5563422 A	19961008	23	Gallium nitride-based III-V group compound semiconductor device and method of producing the same	257/13	257/103 ; 257/22 ; 257/615 ; 257/741 ; 257/745 ; 257/750 ; 257/751 ; 257/76 ; 257/763 ; 257/764 ; 257/765 ; 257/766 ; 257/770 ; 257/771 ; 257/79	Nakamura, Shuji , et al.
US 5578839 A	19961126	19	Light-emitting gallium nitride-based compound semiconductor device	257/96	257/101 ; 257/201 ; 257/613	Nakamura, Shuji , et al.
US 5585648 A	19961217	16	High brightness electroluminescent device, emitting in the green to ultraviolet spectrum, and method of making the same	257/77	257/103 ; 257/627 ; 257/94 ; 372/43 ; 372/45 ; 438/32 ; 438/42	Tischler, Michael A.